

DB-1 SILICON BRIDGE RECTIFIER

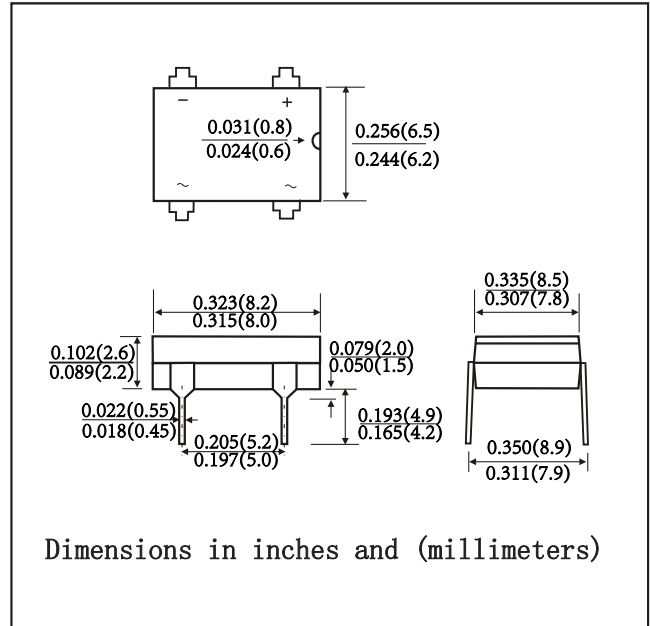
REVERSE VOLTAGE: 50 --- 1000V CURRENT: 1.5A

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Glass passivated chip junction
- Rating to 1000V PRV
- Ideal for printed circuit board
- High temperature soldering guaranteed :260 °C/ 10s seconds at terminals
- Component in accordance to ROHS 2015/863 and WEEE2012/19/EU

MECHANICAL DATA

- Case: DB-1 molded plastic body
- Epoxy: UL94V-0 rate flame retardant
- Terminals: Plated leads solderable per MIL-STD-750, method 2026
- Mounting position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

Parameter	Symbols	DB151	DB152	DB153	DB154	DB155	DB156	DB157	Units
		DF 15005	DF 1501	DF 1502	DF 1504	DF 1506	DF 1508	DF 1510	
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	Volts
Maximum Average Forward Rectified Current	I(AV)	1.5							Amp
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I _{FSM}	50							Amps
Maximum Instantaneous Forward Voltage at 1I _A DC	V _F	1.1							Volts
Maximum DC Reverse Current at rated DC blocking voltage	T _A =25 °C	10							μA
	T _A =125 °C	500							
Typical junction capacitance(Note 1)	C _J	25							pF
Typical thermal resistance(Note 2) Operating	R _{θJA}	40							K/W
junction and storage temperature range	T _J T _{STG}	-55 to +150							°C

RATINGS AND CHARACTERISTIC CURVES

FIG.1-TYPRCAL FORWARD CURRENT DERATING CURVE

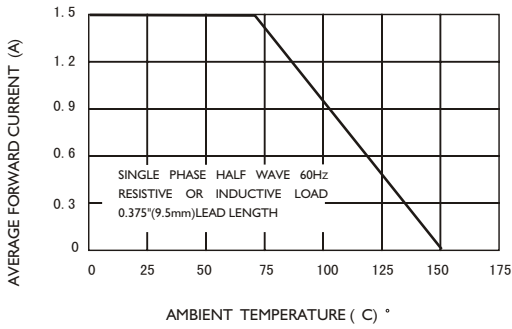


FIG.2-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

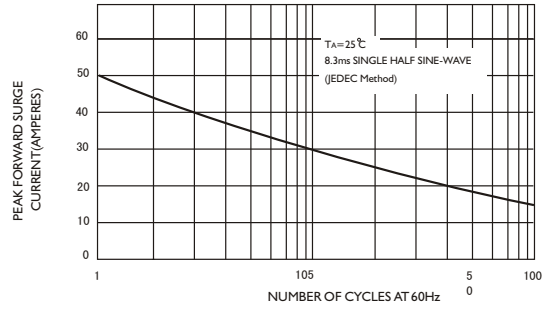


FIG.3-TYPICAL JUNCTION CAPACITANCE

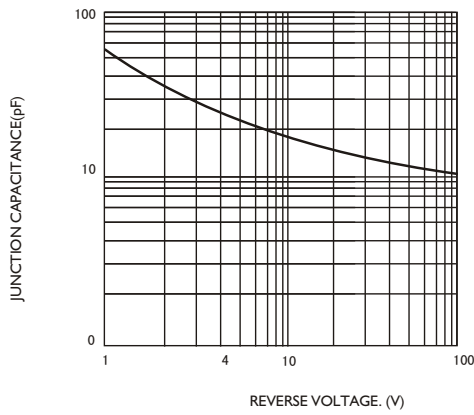


FIG.4-TYPICAL FORWARD CHARACTERISTICS

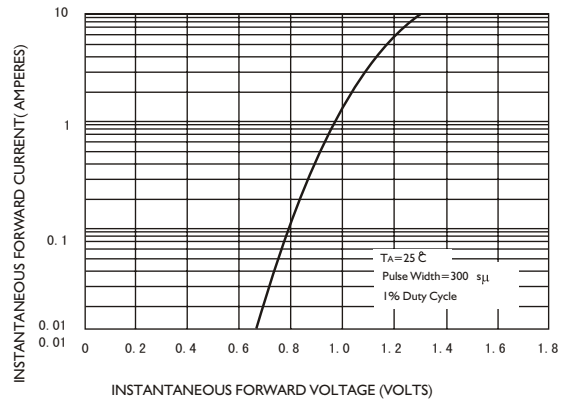


FIG.5-TYPICAL REVERSE CHARACTERISTICS

